

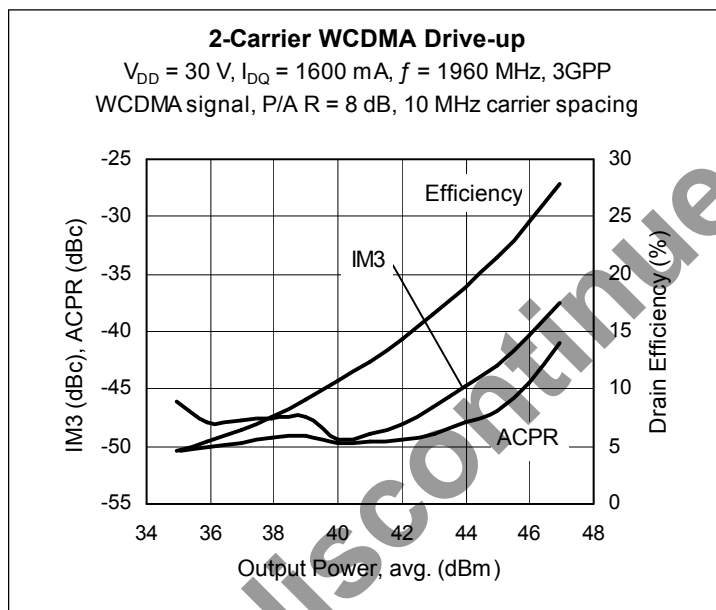
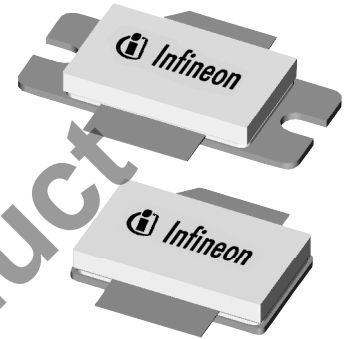
## Thermally-Enhanced High Power RF LDMOS FETs 200 W, 1930 – 1990 MHz

### Description

The PTFA192001E and PTFA192001F are 200-watt LDMOS FETs intended for single- and two-carrier WCDMA and CDMA applications from 1930 to 1990 MHz. Features include input and output matching, and thermally-enhanced packages with slotted or earless flanges. Manufactured with Infineon's advanced LDMOS process, these devices provide excellent thermal performance and superior reliability.

PTFA192001E  
Package H-36260-2

PTFA192001F  
Package H-37260-2



### Features

- Pb-free, RoHS-compliant and thermally-enhanced packages
- Broadband internal matching
- Typical two-carrier WCDMA performance at 1990 MHz, 30 V
  - Average output power = 47.0 dBm
  - Linear Gain = 15.9 dB
  - Efficiency = 27%
  - Intermodulation distortion = -36 dBc
  - Adjacent channel power = -41 dBc
- Typical single-carrier WCDMA performance at 1960 MHz, 30 V, 3GPP signal, P/AR = 7.5 dB
  - Average output power = 48.5 dBm
  - Linear Gain = 15.9 dB
  - Efficiency = 34%
  - Intermodulation distortion = -37 dBc
  - Adjacent channel power = -40 dBc
- Typical CW performance, 1960 MHz, 30 V
  - Output power at P-1dB = 240 W
  - Efficiency = 57%
- Integrated ESD protection: Human Body Model, Class 2 (minimum)
- Excellent thermal stability, low HCI drift
- Capable of handling 5:1 VSWR @ 30 V, 200 W (CW) output power

All published data at  $T_{CASE} = 25^{\circ}\text{C}$  unless otherwise indicated

**ESD:** Electrostatic discharge sensitive device—observe handling precautions!

## RF Characteristics

### WCDMA Measurements (tested in Infineon test fixture)

$V_{DD} = 30\text{ V}$ ,  $I_{DQ} = 1.8\text{ A}$ ,  $P_{OUT} = 50\text{ W}$  average

$f_1 = 1985\text{ MHz}$ ,  $f_2 = 1995\text{ MHz}$ , 3GPP signal, channel bandwidth = 3.84 MHz, peak/average = 8 dB @ 0.01% CCDF

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	$G_{ps}$	15.3	15.9	—	dB
Drain Efficiency	$\eta_D$	26.5	27	—	%
Intermodulation Distortion	IMD	—	-36	-34	dBc

### Two-tone Measurements (not subject to production test—verified by design/characterization in Infineon test fixture)

$V_{DD} = 30\text{ V}$ ,  $I_{DQ} = 1.6\text{ A}$ ,  $P_{OUT} = 200\text{ W}$  PEP,  $f = 1960\text{ MHz}$ , tone spacing = 1 MHz

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	$G_{ps}$	—	15.9	—	dB
Drain Efficiency	$\eta_D$	—	41	—	%
Intermodulation Distortion	IMD	—	-30	—	dBc

## DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$ , $I_{DS} = 10\text{ mA}$	$V_{(BR)DSS}$	65	—	—	V
Drain Leakage Current	$V_{DS} = 28\text{ V}$ , $V_{GS} = 0\text{ V}$	$I_{DSS}$	—	—	1.0	$\mu\text{A}$
Drain Leakage Current	$V_{DS} = 63\text{ V}$ , $V_{GS} = 0\text{ V}$	$I_{DSS}$	—	—	10.0	$\mu\text{A}$
On-State Resistance	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.05	—	$\Omega$
Operating Gate Voltage	$V_{DS} = 30\text{ V}$ , $I_{DQ} = 1.8\text{ A}$	$V_{GS}$	2.0	2.5	3.0	V
Gate Leakage Current	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0\text{ V}$	$I_{GSS}$	—	—	1.0	$\mu\text{A}$

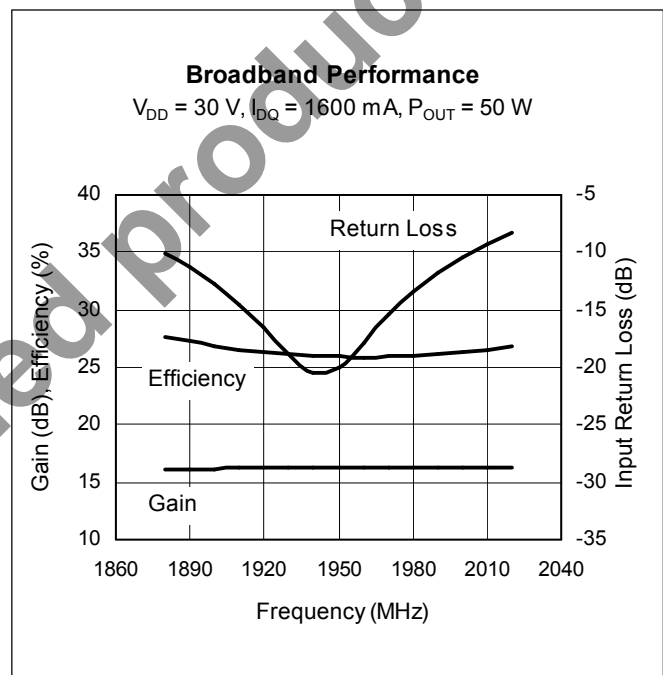
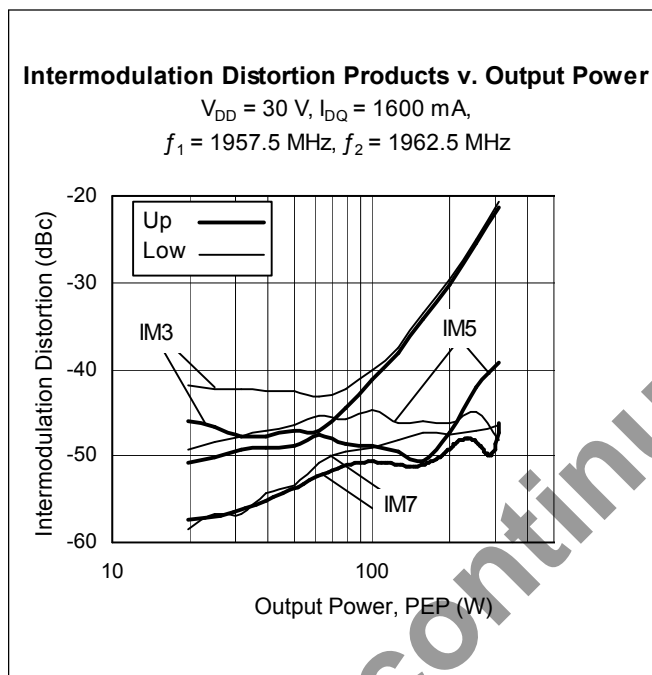
## Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	65	V
Gate-Source Voltage	$V_{GS}$	-0.5 to +12	V
Junction Temperature	$T_J$	200	$^{\circ}\text{C}$
Total Device Dissipation	$P_D$	625	W
Above 25 $^{\circ}\text{C}$ derate by		3.57	W/ $^{\circ}\text{C}$
Storage Temperature Range	$T_{STG}$	-40 to +150	$^{\circ}\text{C}$
Thermal Resistance ( $T_{CASE} = 70^{\circ}\text{C}$ , 200 W CW)	$R_{\theta JC}$	0.28	$^{\circ}\text{C}/\text{W}$

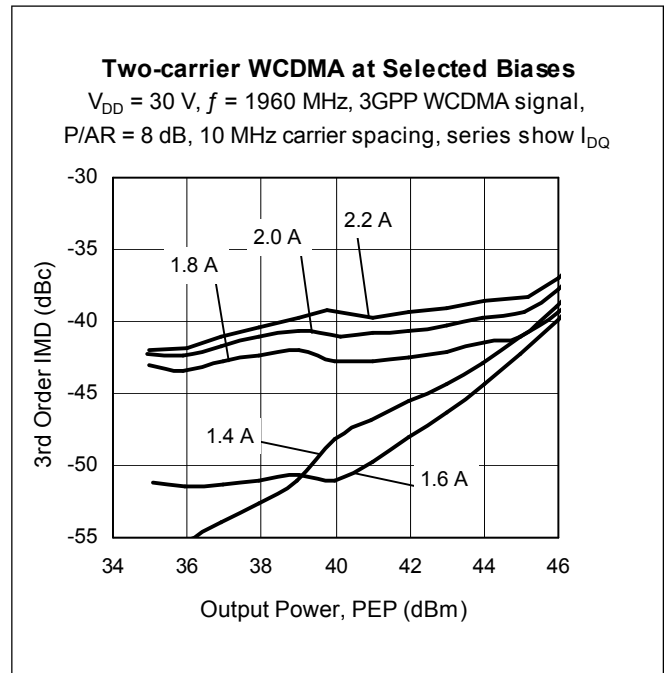
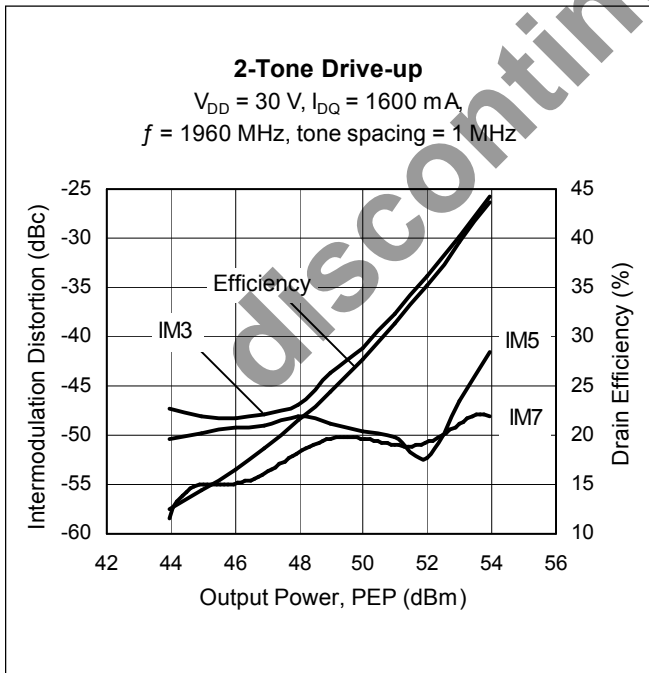
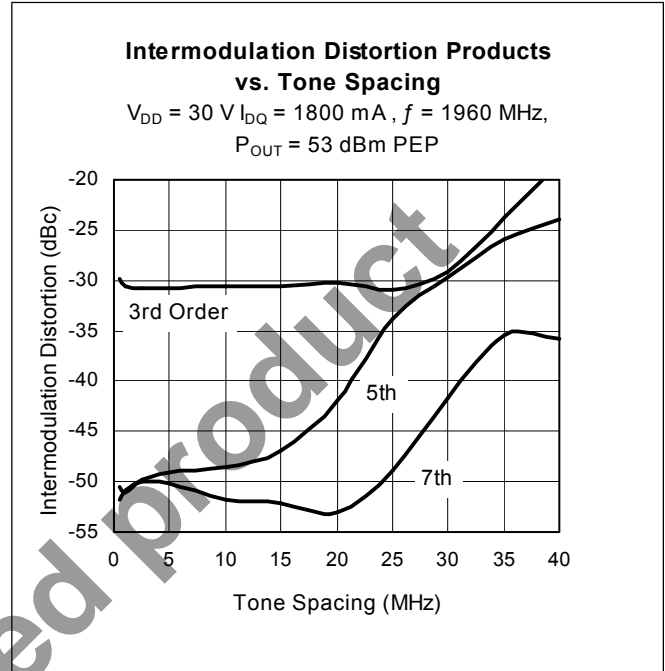
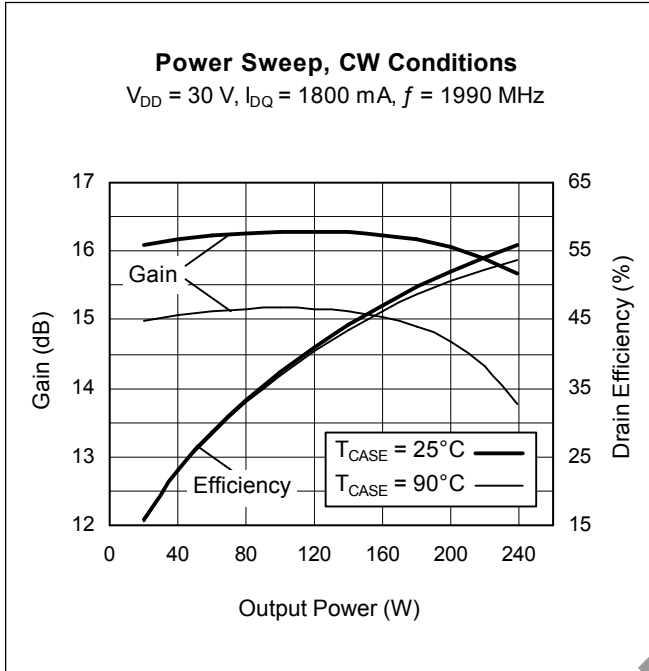
### Ordering Information

Type and Version	Package Type	Package Description	Marking
PTFA192001E V4	H-36260-2	Thermally-enhanced slotted flange, single-ended	PTFA192001E
PTFA192001F V4	H-37260-2	Thermally-enhanced earless flange, single-ended	PTFA192001F

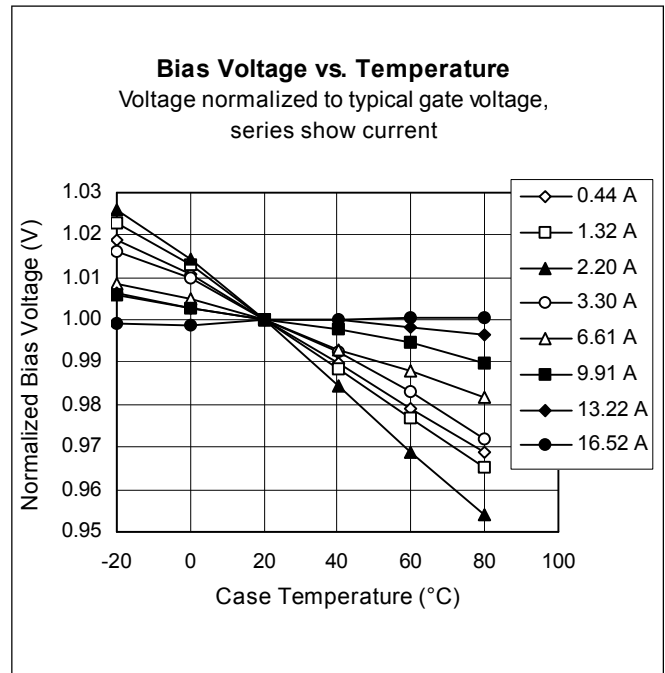
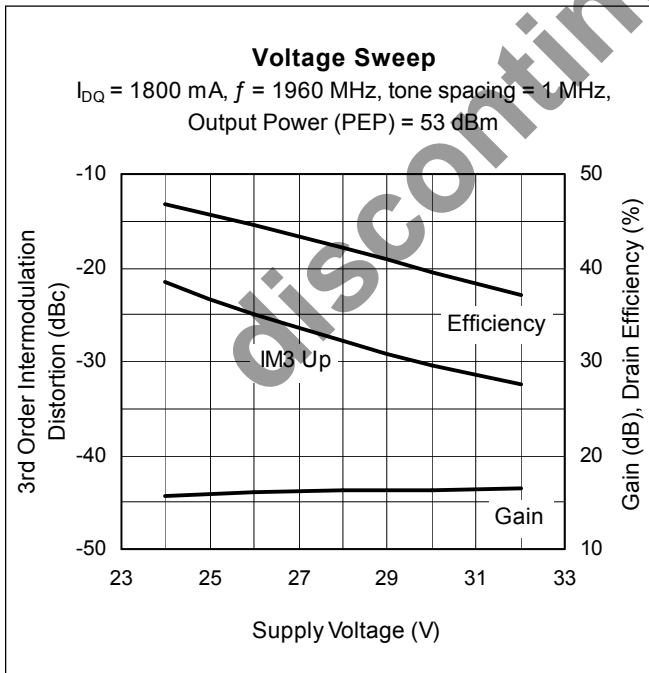
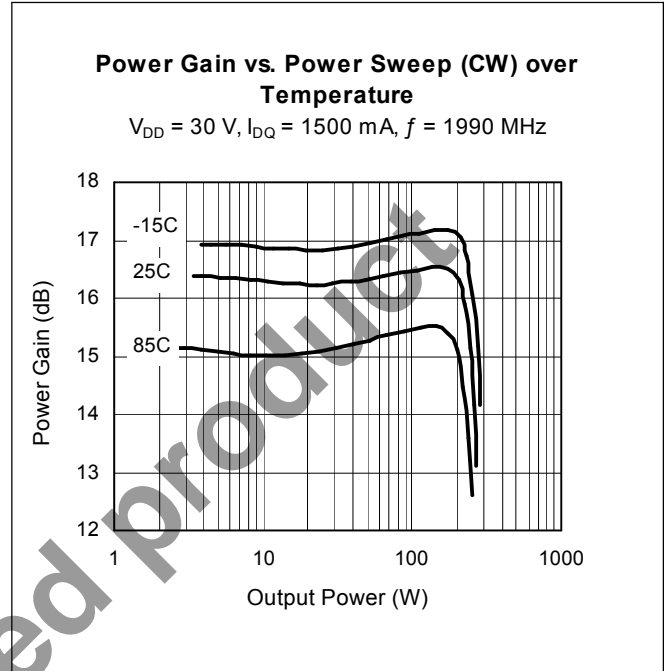
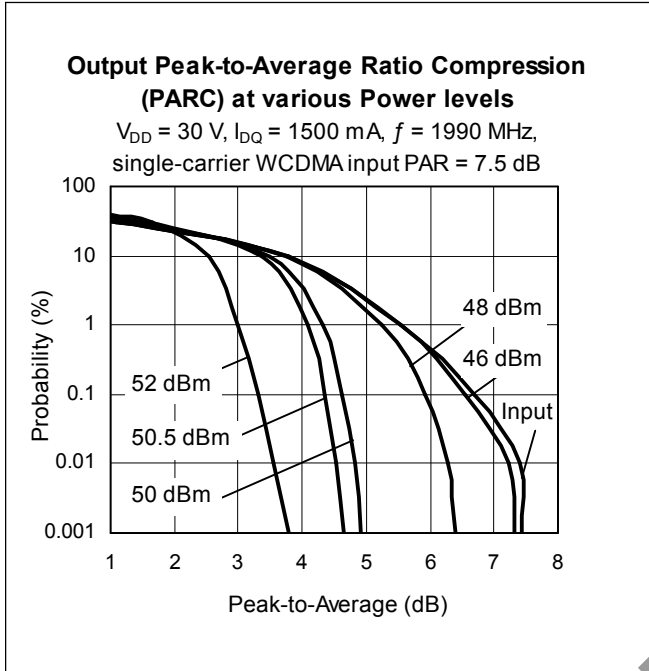
### Typical Performance (data taken in a production test fixture)



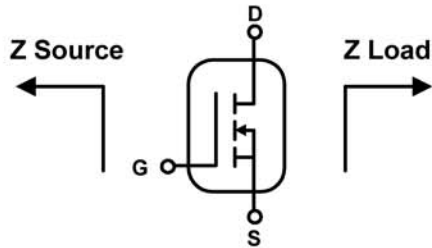
Typical Performance (cont.)



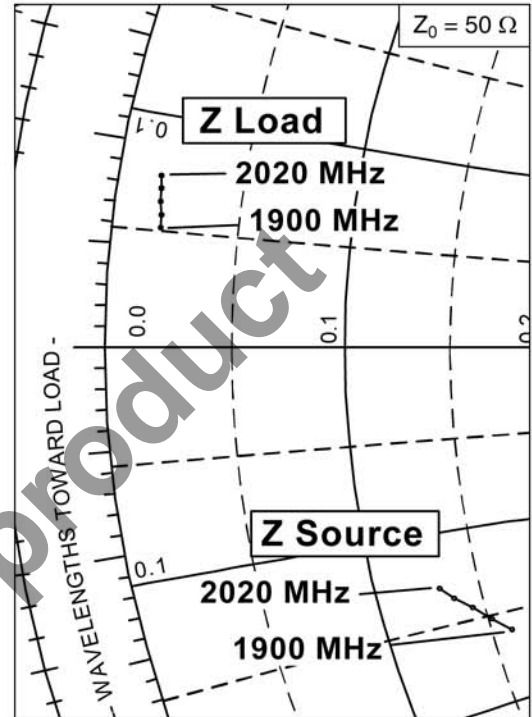
Typical Performance (cont.)



### Broadband Circuit Impedance



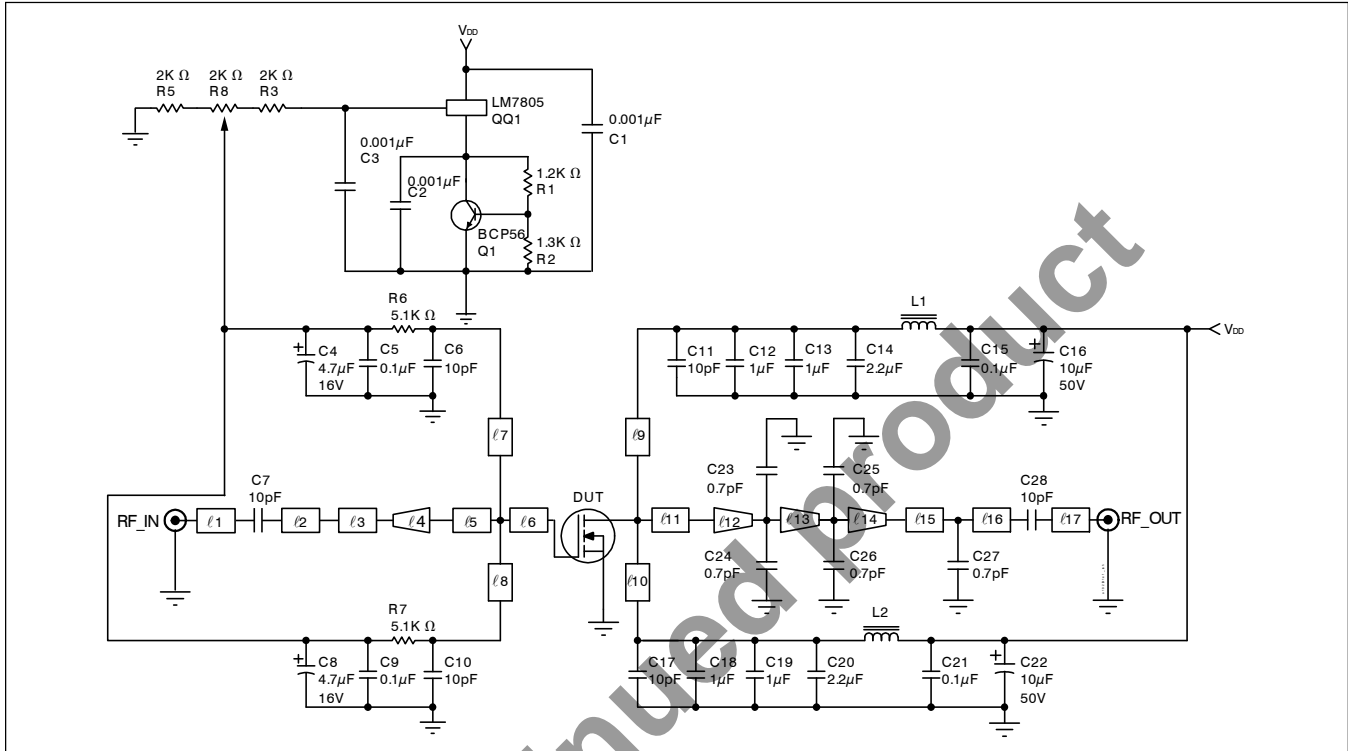
Frequency MHz	Z Source $\Omega$		Z Load $\Omega$	
	R	jX	R	jX
1900	8.033	-8.054	0.943	2.60
1930	7.611	-7.612	0.932	2.87
1960	7.230	-7.197	0.886	3.15
1990	6.839	-6.839	0.863	3.44
2020	6.541	-6.496	0.829	3.71



See next page for circuit information

discontinued product

## Reference Circuit



Reference circuit schematic for  $f = 1960 \text{ MHz}$

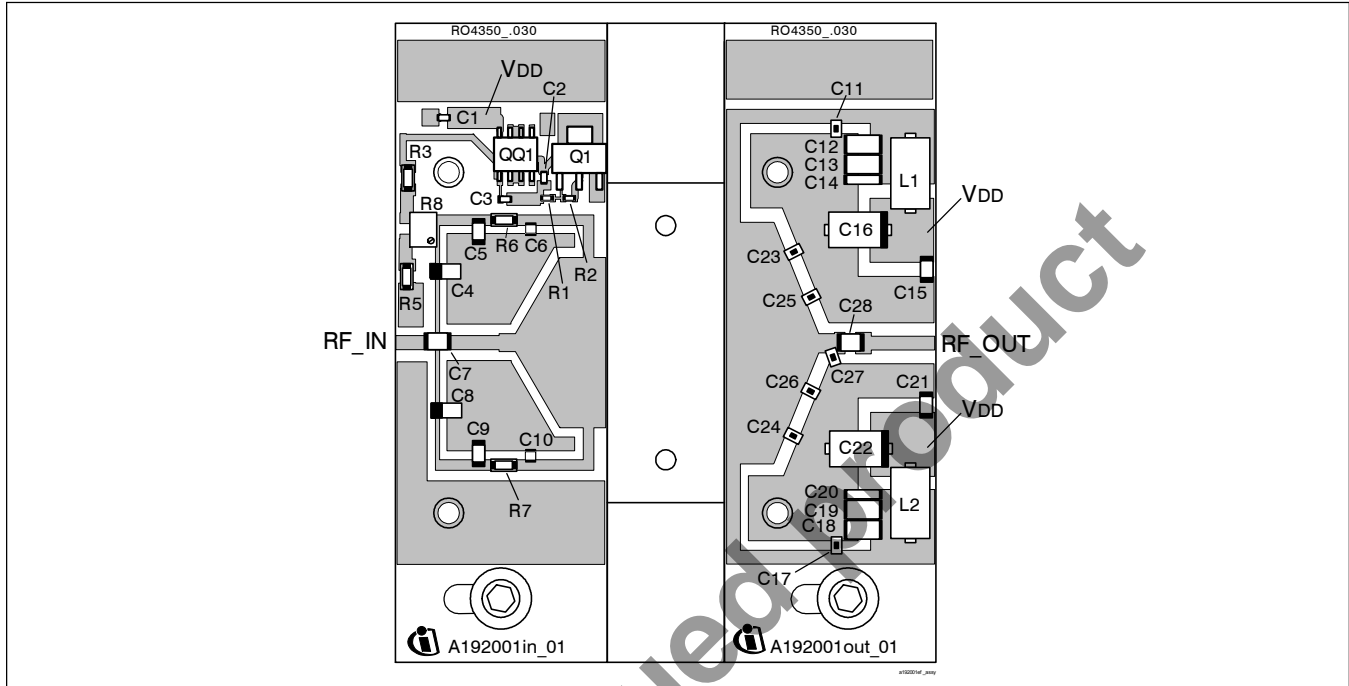
### Circuit Assembly Information

DUT	PTFA192001E or PTFA192001F	LDMOS Transistor	
PCB	0.76 mm [.030"] thick, $\epsilon_r = 3.48$	Rogers RO4350	1 oz. copper

Microstrip	Electrical Characteristics at 1960 MHz <sup>1</sup>	Dimensions: L x W ( mm )	Dimensions: L x W ( in. )
l1	0.038 $\lambda$ , 50.0 $\Omega$	3.51 x 1.70	0.138 x 0.067
l2	0.071 $\lambda$ , 50.0 $\Omega$	6.60 x 1.70	0.260 x 0.067
l3	0.022 $\lambda$ , 43.0 $\Omega$	2.01 x 2.16	0.079 x 0.085
l4 (taper)	0.060 $\lambda$ , 43.0 $\Omega$ / 6.9 $\Omega$	5.28 x 2.16 / 20.32	0.208 x 0.085 / 0.800
l5	0.040 $\lambda$ , 6.9 $\Omega$	3.33 x 20.32	0.131 x 0.800
l6	0.026 $\lambda$ , 6.9 $\Omega$	2.21 x 20.32	0.087 x 0.800
l7, l8	0.123 $\lambda$ , 60.0 $\Omega$	11.48 x 1.24	0.452 x 0.049
l9, l10	0.258 $\lambda$ , 50.9 $\Omega$	23.88 x 1.65	0.940 x 0.065
l11	0.067 $\lambda$ , 5.0 $\Omega$	5.59 x 28.91	0.220 x 1.138
l12 (taper)	0.017 $\lambda$ , 5.0 $\Omega$ / 7.2 $\Omega$	1.42 x 28.91 / 19.51	0.056 x 1.138 / 0.768
l13 (taper)	0.024 $\lambda$ , 7.2 $\Omega$ / 12.3 $\Omega$	2.08 x 19.51 / 10.67	0.082 x 0.768 / 0.420
l14 (taper)	0.019 $\lambda$ , 12.3 $\Omega$ / 41 $\Omega$	1.78 x 10.67 / 2.29	0.070 x 0.420 / 0.090
l15	0.009 $\lambda$ , 41.0 $\Omega$	0.79 x 2.29	0.031 x 0.090
l16	0.021 $\lambda$ , 41.0 $\Omega$	1.85 x 2.29	0.073 x 0.090
l17	0.096 $\lambda$ , 50.0 $\Omega$	8.99 x 1.70	0.354 x 0.067

<sup>1</sup>Electrical characteristics are rounded.

Reference Circuit (cont.)



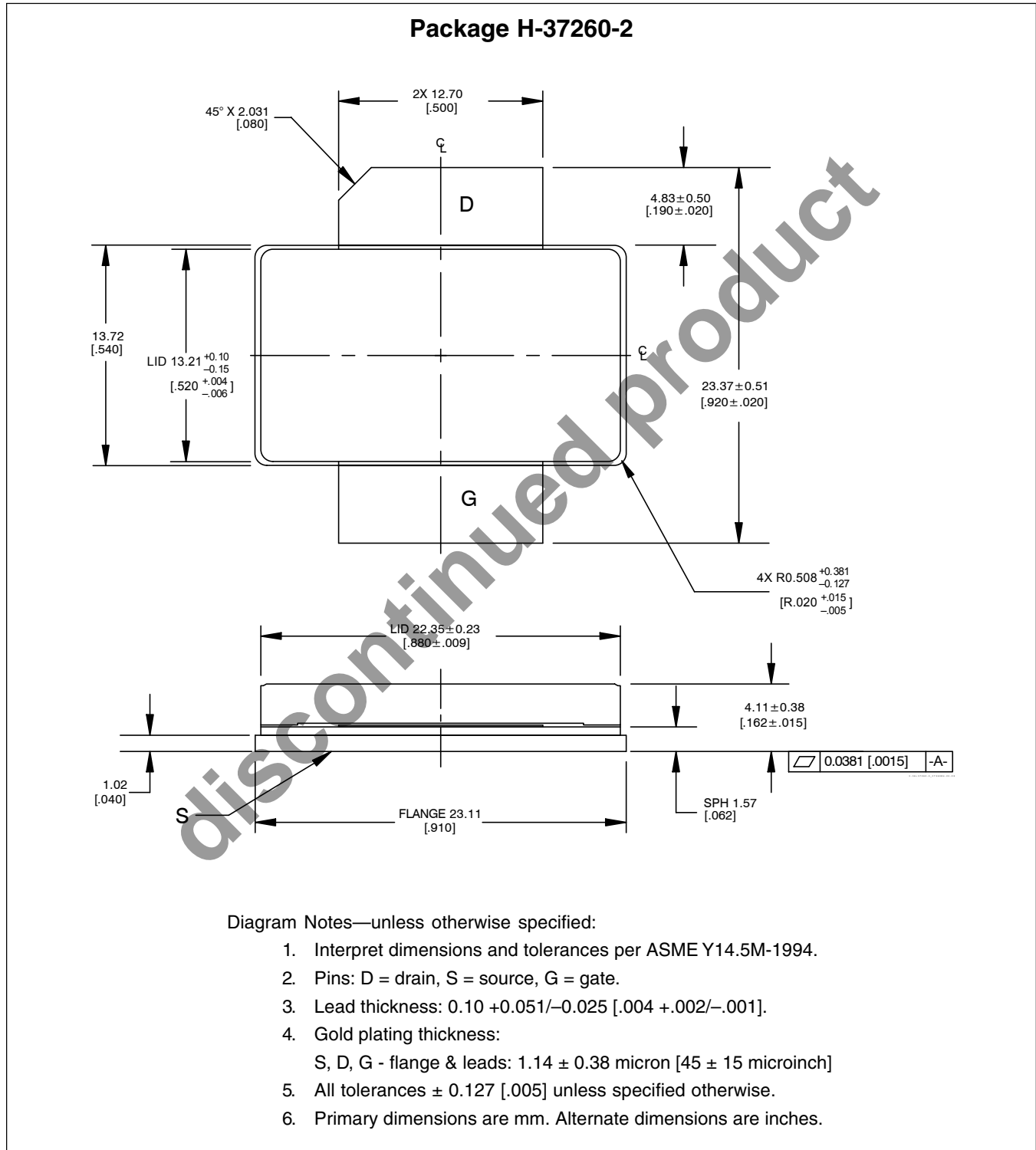
Reference circuit assembly diagram\* (not to scale)

Component	Description	Suggested Manufacturer	P/N or Comment
C1, C2, C3	Capacitor, 0.001 $\mu$ F	Digi-Key	PCC1772CT-ND
C4, C8	Capacitor, 4.7 $\mu$ F, 16 V	Digi-Key	PCS3475CT-ND
C5, C9, C15, C21	Capacitor, 0.1 $\mu$ F	Digi-Key	PCC104BCT-ND
C6, C10	Ceramic capacitor, 10 pF	ATC	100A 100
C7, C28	Ceramic capacitor, 10 pF	ATC	100B 100
C11, C17	Capacitor, 10 pF	AVX	08051J100GBTTR
C12, C13, C18, C19	Ceramic capacitor, 1 $\mu$ F	Digi-Key	445-1411-1-ND
C14, C20	Capacitor, 2.2 $\mu$ F	Digi-Key	445-1447-2-ND
C16, C22	Tantalum capacitor, 10 $\mu$ F, 50 V	Garrett Electronics	TPSE106K050R0400
C23, C24, C25, C26, C27	Capacitor, 0.7 pF	AVX	08051J0R7BBTTR
L1, L2	Ferrite, 8.9 mm	Elna Magnetics	BDS 4.6/3/8.9-4S2
Q1	Transistor	Infineon Technologies	BCP56
QQ1	Voltage regulator	National Semiconductor	LM7805
R1	Chip resistor 1.2 k-ohms	Digi-Key	P1.2KGCT-ND
R2	Chip resistor 1.3 k-ohms	Digi-Key	P1.3KGCT-ND
R3, R5	Chip resistor 2 k-ohms	Digi-Key	P2KECT-ND
R6, R7	Chip resistor 5.1 k-ohms	Digi-Key	P5.1KECT-ND
R8	Potentiometer 2 k-ohms	Digi-Key	3224W-202ETR-ND

\*Gerber files for this circuit available on request



Package Outline Specifications (cont.)



Find the latest and most complete information about products and packaging at the Infineon Internet page  
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Revision History: 2017-07-19

Data Sheet

Previous Version: 2015-03-04, Data Sheet

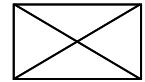
Page	Subjects (major changes since last revision)
All	Product discontinued

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